

# 12F/12FR

## 12AMP SILICON POWER DIODE



**NAINA**

DO-4

12F/ 12FR

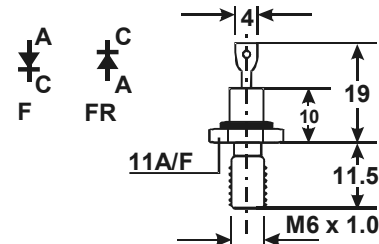
### FEATURES

- All Diffused Series
- Available in Normal & Reverse Polarity
- Industrial Grade
- Available In Avalanche Characteristic

\* Available in metric and UNF thread

### ELECTRICAL SPECIFICATIONS

		12F/FR
$I_F$ (A)	Maximum Average Forward Current $T_c=150^\circ\text{C}$	12A
$V_{FM}$	Maximum peak forward voltage drop @ Rated $I_{F(AV)}$	1.2V
$I_{FSM}$	Maximum peak one cycle (non-rep) surge current 10msec	250 A
$I_{FRM}$	Maximum peak one cycle (non-rep) surge current 10msec	60 A
$I^2t$	Maximum $I^2t$ rating (non-rep.) for 5 to 10 m sec.	250A <sup>2</sup> Sec



### THERMAL MECHANICAL SPECIFICATIONS

$\theta_{JC}$	Maximum thermal resistance Junction to case	2°C/W
$T_J$	Operating Junction Temp.	-65°C to 150°C
$T_{stg}$	Storage temperature	-65°C to 150°C
	Mounting torque (non-lubricated threads)	0.14 M-Kg min, 0.17 M-Kg max
W	Approx, weight	7 gms.

### ELECTRICAL RATINGS

TYPE	12F/12FR	10	20	40	60	80	100	120	140	160
$V_{RRM}$	Max. repetitive peak voltage (v)	100	200	400	600	800	1000	1200	1400	1600
$V_R$ (RMS)	Max. R.M.S. reverse voltage (V)	70	140	280	420	560	700	840	980	1120
$V_R$	Max. D.C. Blocking Voltage (V)	100	200	400	600	800	1000	1200	1400	1600
	Recommended R.M.S. working Voltage(v)	40	80	160	240	320	400	480	560	640
$I_R$ (AV)	Max. Average reverse leakage current @ $V_{RRM}$ $T_c$ 25°C uA	100	100	100	100	100	100	100	100	100

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